

# **BSS84AKS**

# 50 V, 160 mA dual P-channel Trench MOSFET Rev. 1 — 23 May 2011

**Product data sheet** 

#### **Product profile** 1.

# 1.1 General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1 kV
- AEC-Q101 qualified

# 1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	istor						
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-50	V
$V_{GS}$	gate-source voltage			-20	-	20	V
$I_D$	drain current	$V_{GS}$ = -10 V; $T_{amb}$ = 25 °C	[1]	-	-	-160	mΑ
Static ch	aracteristics (per transis	tor)					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -10 \text{ V; } I_D = -100 \text{ mA;}$ $T_j = 25 \text{ °C}$		-	4.5	7.5	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



# 50 V, 160 mA dual P-channel Trench MOSFET

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1	D. D. D.	D4 D0
2	G1	gate 1	6   5   4	D1 D2
3	D2	drain 2		
4	S2	source 2	0	G1 + G2
5	G2	gate 2	□1 □2 □3	
6	D1	drain 1	SOT363 (TSSOP6)	S1 S2
				S1 32 sym147

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS84AKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BSS84AKS	%VY

[1] % = placeholder for manufacturing site code

# 50 V, 160 mA dual P-channel Trench MOSFET

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
Per transis	tor						
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-50	V	
$V_{GS}$	gate-source voltage			-20	20	V	
I <sub>D</sub>	drain current	$V_{GS}$ = -10 V; $T_{amb}$ = 25 °C	<u>[1]</u>	-	-160	mΑ	
		V <sub>GS</sub> = -10 V; T <sub>amb</sub> = 100 °C	<u>[1]</u>	-	-100	mΑ	
I <sub>DM</sub>	peak drain current	$T_{amb} = 25 \text{ °C}$ ; single pulse; $t_p \le 10 \text{ µs}$		-	-640	mΑ	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	280	mW	
			[1]	-	320	mW	
		T <sub>sp</sub> = 25 °C		-	990	mW	
Per device							
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	445	mW	
Tj	junction temperature			-55	150	°C	
T <sub>amb</sub>	ambient temperature			-55	150	°C	
T <sub>stg</sub>	storage temperature			-65	150	°C	
Source-dra	in diode						
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	-160	mA	
ESD maximum rating							
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[3]	-	1000	V	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

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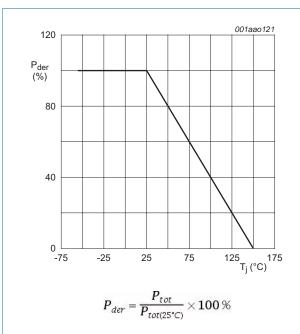


Fig 1. Normalized total power dissipation as a function of junction temperature

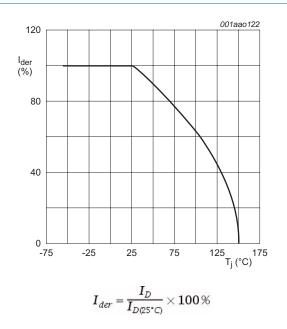
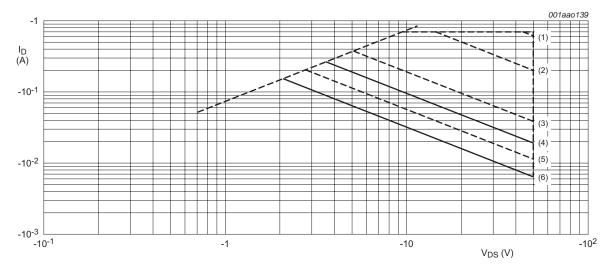


Fig 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> is single pulse

(1)  $t_p = 100 \ \mu s$ 

(2)  $t_p = 1 \text{ ms}$ 

(3)  $t_p = 10 \text{ ms}$ 

(4) DC;  $T_{sp} = 25$  °C

 $(5) t_p = 100 ms$ 

(6) DC;  $T_{amb} = 25$  °C; drain mounting pad 1 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 50 V, 160 mA dual P-channel Trench MOSFET

# 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	300	K/W
Per transist	tor						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	390	445	K/W
			[2]	-	340	390	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	130	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

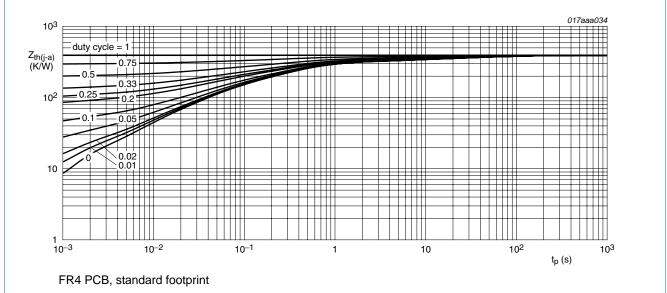


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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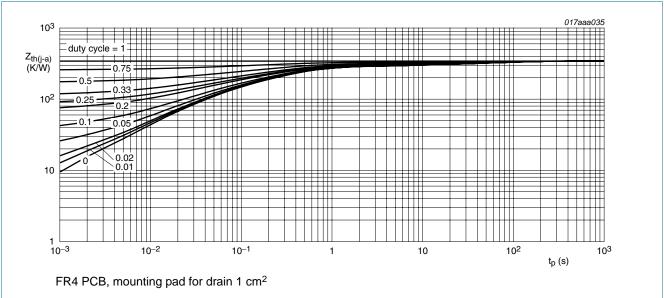


Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 50 V, 160 mA dual P-channel Trench MOSFET

# 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -10 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-50	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-1.1	-1.6	-2.1	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -50 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	-2	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	4.5	7.5	Ω
	resistance	$V_{GS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 150 \text{ °C}$	-	8	13.5	Ω
		$V_{GS} = -5 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	5.7	8.5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -100 \text{ mA}; T_j = 25 \text{ °C}$	-	150	-	mS
Dynamic	characteristics (per transistor)					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = -25 \text{ V}; I_D = -200 \text{ mA}; V_{GS} = -5 \text{ V};$	-	0.26	0.35	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.09	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = -25 \text{ V; } f = 1 \text{ MHz; } V_{GS} = 0 \text{ V;}$	-	24	36	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.5	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.3	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -30 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = -10 V;	-	13	26	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	11	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	48	96	ns
t <sub>f</sub>	fall time		-	25	-	ns
Source-di	rain diode (per transistor)					
$V_{SD}$	source-drain voltage	$I_S = -115 \text{ mA}; V_{GS} = 0 \text{ V}; T_i = 25 \text{ °C}$	-0.48	-0.85	-1.2	V

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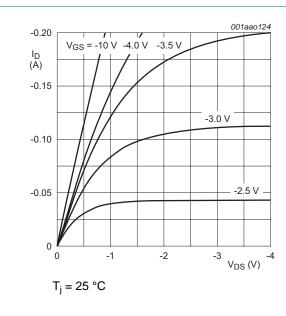
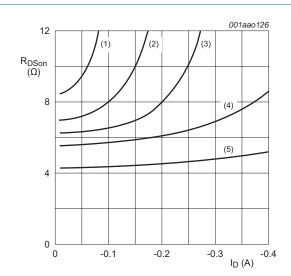


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

(1)  $V_{GS} = -3.0 \text{ V}$ 

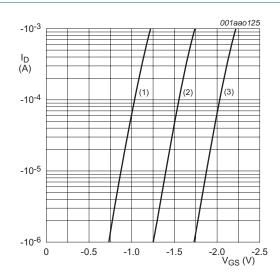
(2)  $V_{GS} = -3.5 \text{ V}$ 

(3)  $V_{GS} = -4.0 \text{ V}$ 

(4)  $V_{GS} = -5.0 \text{ V}$ 

(5)  $V_{GS} = -10.0 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



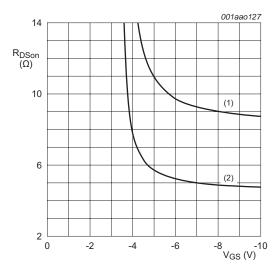
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



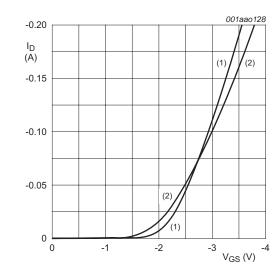
 $I_D = -200 \text{ mA}$ 

(1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}\text{C}$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

# 50 V, 160 mA dual P-channel Trench MOSFET

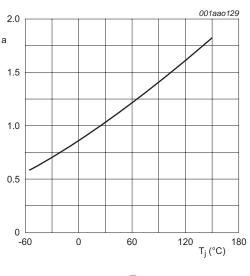


 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_j = 25 \, ^{\circ}C$$

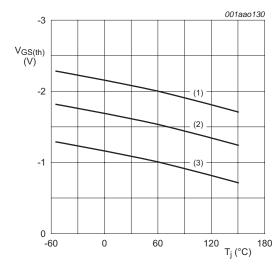
(2)  $T_i = 150 \, ^{\circ}\text{C}$ 

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$ 

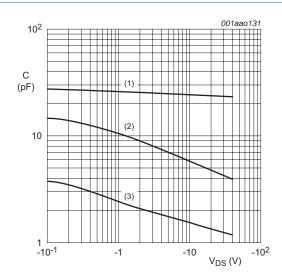
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

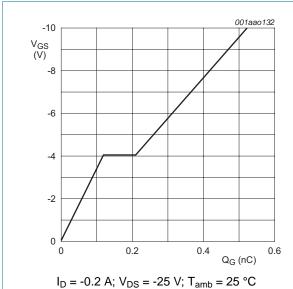


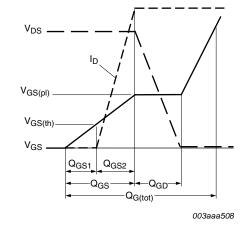
 $f = 1 MHz, V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

# 50 V, 160 mA dual P-channel Trench MOSFET

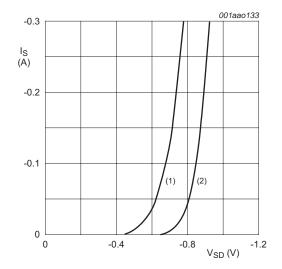




Gata-source voltage as a function of

Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

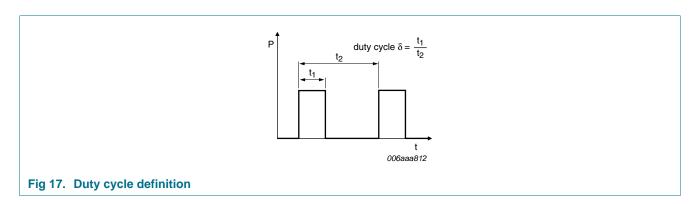
(1)  $T_j = 150 \, ^{\circ}\text{C}$ 

(2)  $T_j = 25 \, ^{\circ}C$ 

Fig 16. Source current as a function of source-drain voltage; typical values

50 V, 160 mA dual P-channel Trench MOSFET

# 8. Test information



# 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

#### 50 V, 160 mA dual P-channel Trench MOSFET

# 9. Package outline

# Plastic surface-mounted package; 6 leads

**SOT363** 

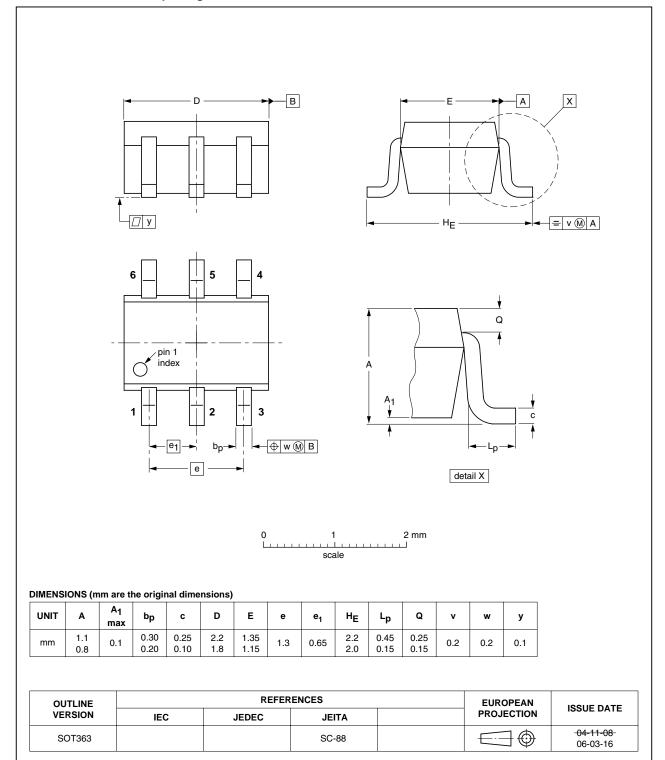


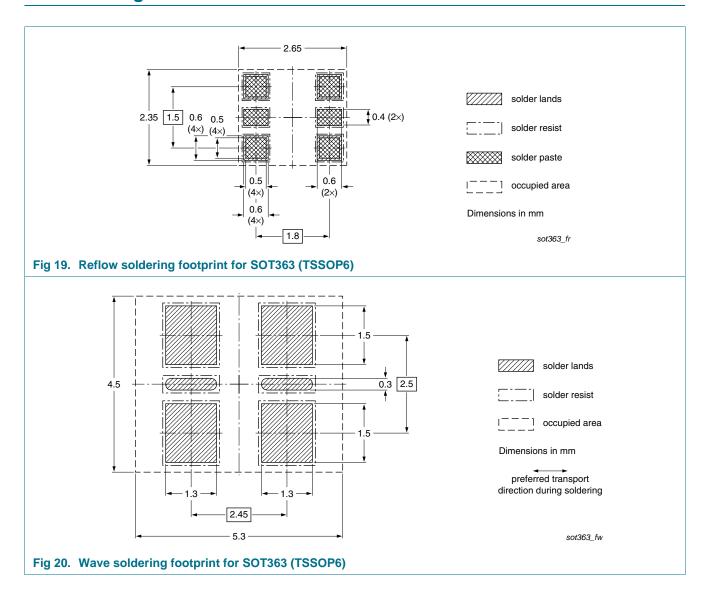
Fig 18. Package outline SOT363 (TSSOP6)

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# 50 V, 160 mA dual P-channel Trench MOSFET

# 10. Soldering



50 V, 160 mA dual P-channel Trench MOSFET

# 11. Revision history

# Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS84AKS v.2	20110523	Product data sheet	-	-

#### 50 V, 160 mA dual P-channel Trench MOSFET

# 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# **BSS84AKS Nexperia** 50 V, 160 mA dual P-channel Trench MOSFET

# 14. Contents

1	Product profile	ı
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	5
7	Characteristics	7
8	Test information11	ı
8.1	Quality information	1
9	Package outline12	2
10	Soldering13	3
11	Revision history14	4
12	Legal information15	5
12.1	Data sheet status	
12.2	Definitions15	5
12.3	Disclaimers	5
12.4	Trademarks16	3
13	Contact information16	ô

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